Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Leadless ultra small and ultra thin SMD plastic package: 1.1 × 1.0 × 0.37 mm
- Exposed drain pad for excellent thermal conduction
- ElectroStatic Discharge (ESD) protection 1 kV HBM
- Drain-source on-state resistance R_{DSon} = 350 mΩ

3. Applications

- High-side load switch and charging switch for portable devices
- Power management in battery driven portables
- LED driver
- DC-to-DC converter

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V	
V_{GS}	gate-source voltage			-8	-	8	V	
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-1.2	Α	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -1.2 \text{ A}; T_j = 25 \text{ °C}$		-	350	447	mΩ	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D I
2	S	source		
3	D	drain	4 3	$G \xrightarrow{\nabla} $
4	D	drain		S S
			Transparent top view DFN1010D-3 (SOT1215)	017aaa259

6. Ordering information

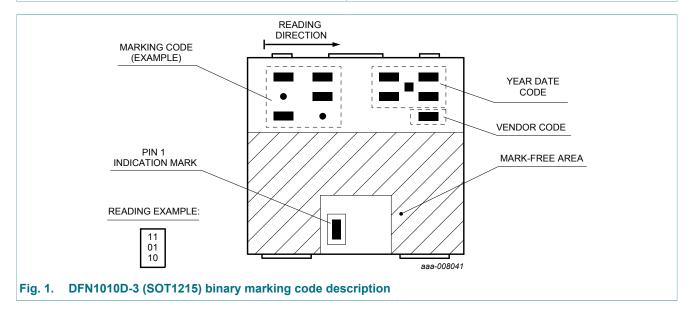
Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMXB350UPE	DFN1010D-3	DFN1010D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 1.1 x 1.0 x 0.37 mm	SOT1215		

7. Marking

Table 4. Marking codes

Type number	Marking code
PMXB350UPE	11 10 00



PMXB350UPE

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit	
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V	
V_{GS}	gate-source voltage			-8	8	V	
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-1.2	Α	
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-1	Α	
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-5	Α	
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	360	mW	
			[1]	-	930	mW	
		T _{sp} = 25 °C		-	5680	mW	
T _j	junction temperature			-55	150	°C	
T _{amb}	ambient temperature			-55	150	°C	
T _{stg}	storage temperature			-65	150	°C	
Source-drain diode							
Is	source current	T _{amb} = 25 °C	[1]	-	-0.9	Α	

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

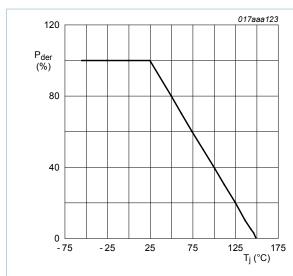


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

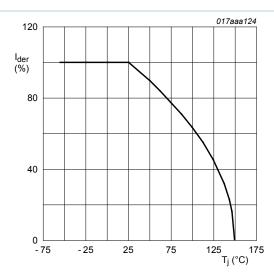


Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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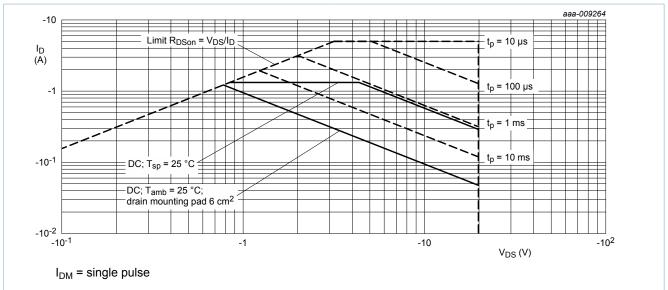


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uily-a)	thermal resistance		[1]	-	303	348	K/W
	from junction to ambient		[2]	-	116	134	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	17	22	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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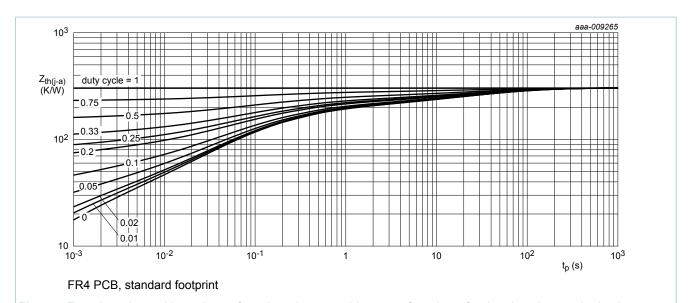


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

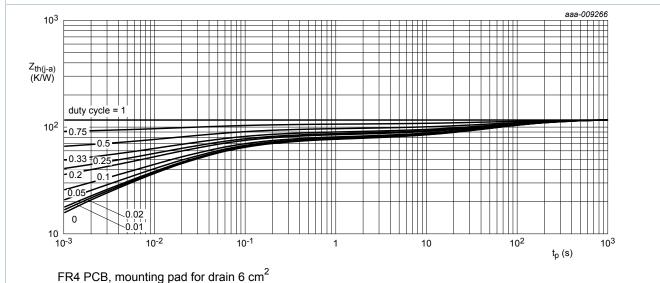


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7 Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
I _{GSS}	gate leakage current	V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I_D = -1.2 A; T_j = 25 °C	-	350	447	mΩ
	resistance	V _{GS} = -4.5 V; I _D = -1.2 A; T _j = 150 °C	-	508	650	mΩ
		V_{GS} = -2.5 V; I_D = -1 A; T_j = 25 °C	-	450	645	mΩ
		V_{GS} = -1.8 V; I_D = -0.4 A; T_j = 25 °C	-	600	940	mΩ
		V_{GS} = -1.5 V; I_D = -10 mA; T_j = 25 °C	-	760	2000	mΩ
		V_{GS} = -1.2 V; I_{D} = -1 mA; T_{j} = 25 °C	-	1200	-	mΩ
9 _{fs}	forward transconductance	V_{DS} = -5 V; I_{D} = -1.2 A; T_{j} = 25 °C	-	5.2	-	S
R _G	gate resistance	f = 1 MHz	-	0.8	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -1.2 A; V_{GS} = -4.5 V;	-	1.25	2.3	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.27	-	nC
Q_{GD}	gate-drain charge		-	0.28	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	116	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	16.5	-	pF
C _{rss}	reverse transfer capacitance		-	12.2	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -1.2 A; V_{GS} = -4.5 V;	-	3	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 ^{\circ}C$	-	9	-	ns
t _{d(off)}	turn-off delay time		-	18	-	ns
t _f	fall time		-	6	-	ns
Source-d	rain diode					,
V _{SD}	source-drain voltage	$I_S = -0.9 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.8	-1.2	V

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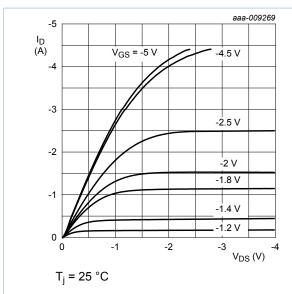


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

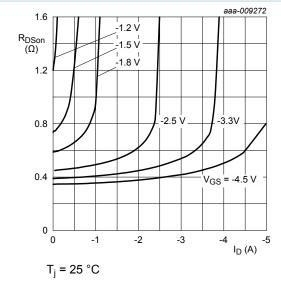


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

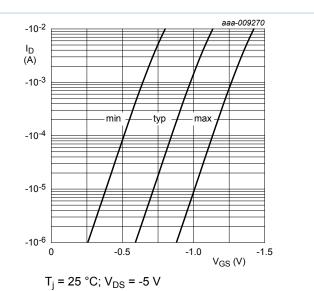


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

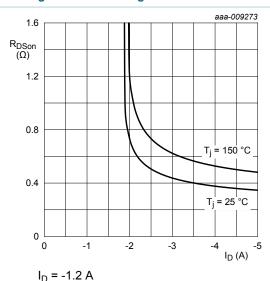


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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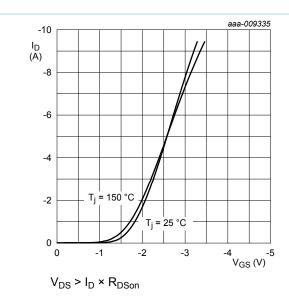


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

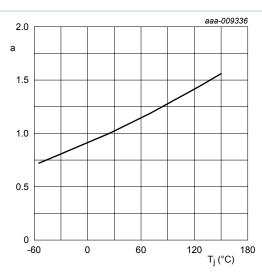


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

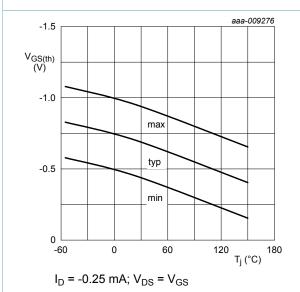
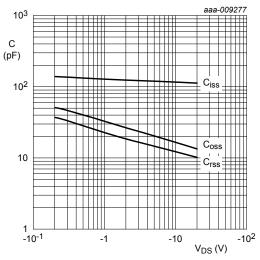


Fig. 13. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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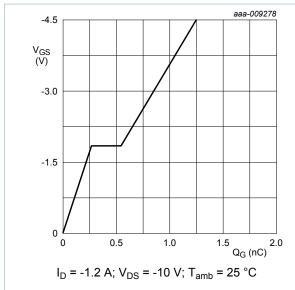


Fig. 15. Gate-source voltage as a function of gate charge; typical values

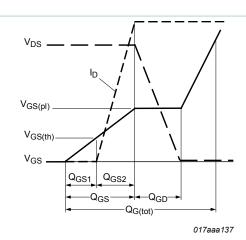


Fig. 16. MOSFET transistor: Gate charge waveform definitions

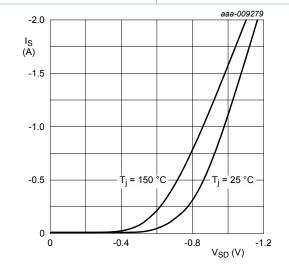
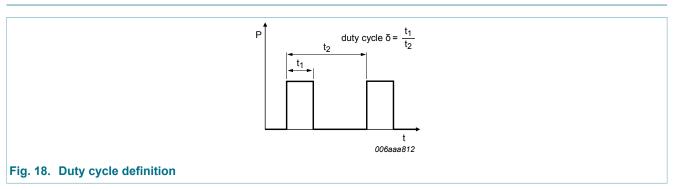


Fig. 17. Source current as a function of source-drain voltage; typical values

11. Test information

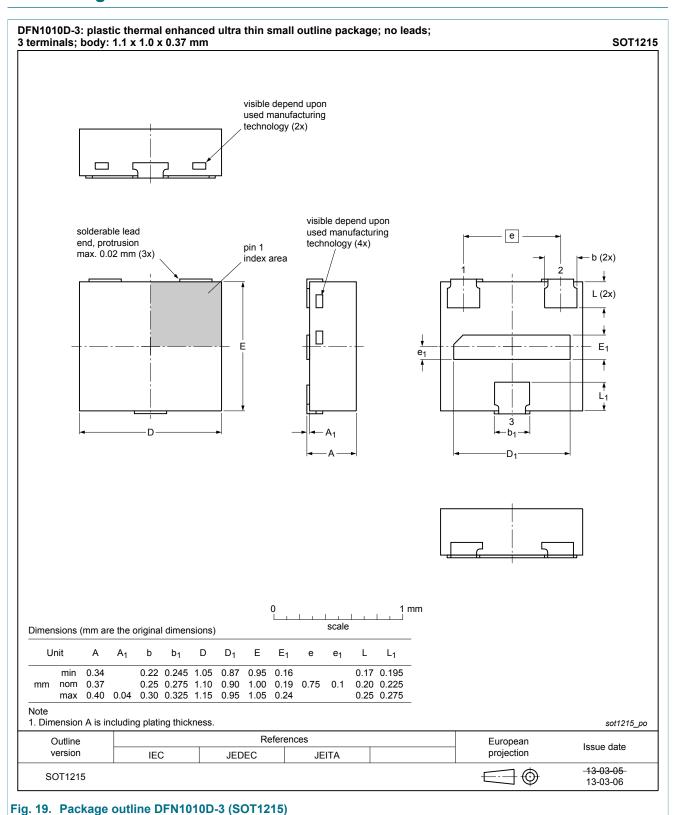
 $V_{GS} = 0 V$



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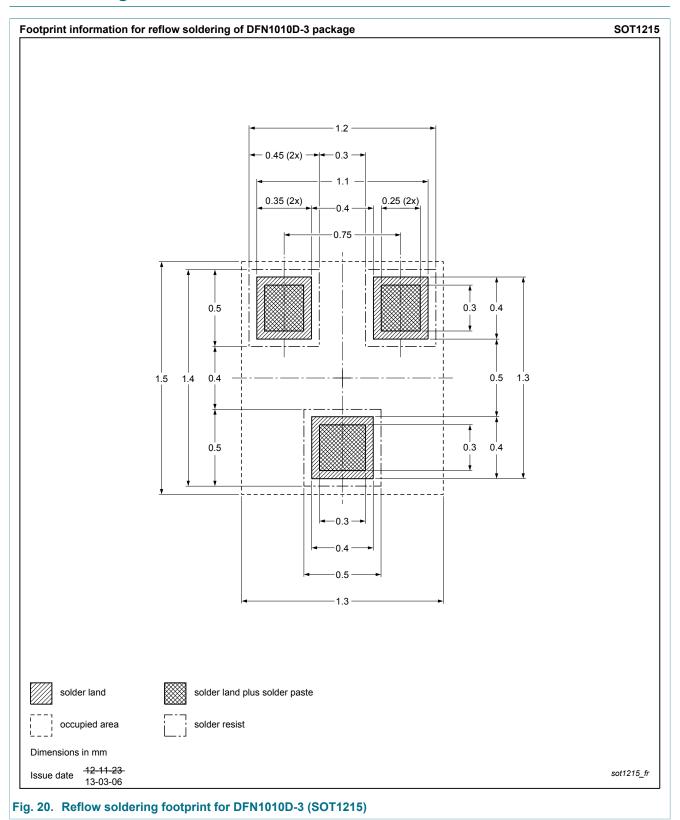
12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMXB350UPE v.2	20140124	Product data sheet	-	PMXB350UPE v.1
Modifications:	Editorial update			
PMXB350UPE v.1	20130919	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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